

Lukas Strizik

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Atomic Layer Deposition Al ₂ O ₃ Coatings Significantly Improve Thermal, Chemical, and Mechanical Stability of Anodic TiO ₂ Nanotube Layers. <i>Langmuir</i> , 2017, 33, 3208-3216.	3.5	44
2	Structural, optical and photoelectrochemical characterizations of monoclinic Ta ₃ N ₅ thin films. <i>Physical Chemistry Chemical Physics</i> , 2015, 17, 23952-23962.	2.8	36
3	Mixed Organotin(IV) Chalcogenides: From Molecules to SnS ₂ Semiconducting Thin Films Deposited by Spin-Coating. <i>Chemistry - A European Journal</i> , 2013, 19, 1877-1881.	3.3	25
4	Green, red and near-infrared photon up-conversion in Ga ₂ Ge ₂ Sb ₂ S:Er ³⁺ amorphous chalcogenides. <i>Journal of Luminescence</i> , 2014, 147, 209-215.	3.1	17
5	MoSe ₂ /TiO ₂ -Coated 1D TiO ₂ Nanotube Layers: Efficient Interface for Light-Driven Applications. <i>Advanced Materials Interfaces</i> , 2018, 5, 1701146.	3.7	16
6	Penn gap rule in phase-change memory materials: No clear evidence for resonance bonds. <i>APL Materials</i> , 2015, 3, .	5.1	14
7	SnS and SnS ₂ thin films deposited using a spin-coating technique from intramolecularly coordinated organotin sulfides. <i>Applied Organometallic Chemistry</i> , 2015, 29, 176-180.	3.5	14
8	Antireflection In ₂ O ₃ coatings of self-organized TiO ₂ nanotube layers prepared by atomic layer deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015, 9, 516-520.	2.4	13
9	Large-area inverse opal structures in a bulk chalcogenide glass by spin-coating and thin-film transfer. <i>Optical Materials</i> , 2013, 36, 390-395.	3.6	10
10	Solution-processed Er ³⁺ -doped As ₃ S ₇ chalcogenide films: optical properties and 1.5 μm photoluminescence activated by thermal treatment. <i>Journal of Materials Chemistry C</i> , 2017, 5, 8489-8497.	5.5	10
11	Dynamics of upconversion photoluminescence in Ge ₂ Ga ₂ S:Er ³⁺ : application of quadrature frequency resolved spectroscopy. <i>Philosophical Magazine Letters</i> , 2015, 95, 466-473.	1.2	8
12	Quadrature frequency resolved spectroscopy of upconversion photoluminescence in GeGaS:Er ³⁺ : I. Determination of energy transfer upconversion parameter. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 7053-7063.	2.2	8
13	Titanocene(IV) and vanadocene(IV) complexes of dicyanomethanidobenzoate. <i>Journal of Organometallic Chemistry</i> , 2009, 694, 4250-4255.	1.8	7
14	Physico-chemical and optical properties of Er ³⁺ -doped and Er ³⁺ /Yb ³⁺ -co-doped Ge ₂₅ Ga _{9.5} Sb _{0.5} S ₆₅ chalcogenide glass. <i>Pure and Applied Chemistry</i> , 2017, 89, 429-436.	1.9	7
15	Quadrature frequency resolved spectroscopy of upconversion photoluminescence in GeGaS:Er ³⁺ : II. elucidating excitation mechanisms of red emission besides green emission. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 7077-7082.	2.2	6
16	In-situ study of athermal reversible photocrystallization in a chalcogenide glass. <i>Journal of Applied Physics</i> , 2017, 122, .	2.5	6
17	Deep red upconversion photoluminescence in Er ³⁺ -doped Yb ₃ Ga ₅ O ₁₂ nanocrystalline garnet. <i>Journal of the American Ceramic Society</i> , 2022, 105, 3391-3402.	3.8	5
18	Influence of thermal history on the photostructural changes in glassy As ₁₅ S ₈₅ studied by Raman scattering and ab initio calculations. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	4

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19	Physico-chemical properties of the thin films of the Sb_xSe_{100-x} system ($x = 90, 85, 80$). <i>Thin Solid Films</i> , 2014, 569, 17-21.	1.8	4
20	Physico-chemical properties of Sb-rich (Sb, In)-Te thin films. <i>Journal of Alloys and Compounds</i> , 2014, 617, 306-309.	5.5	4
21	1.2 μ m and 1.5 μ m near-infrared photoluminescence and visible upconversion photoluminescence in GeGaS:Er ³⁺ /Ho ³⁺ glasses under 980 nm excitation. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 17314-17322.	2.2	4
22	1.5 μ m photoluminescence and upconversion photoluminescence in GeGaAsS:Er chalcogenide glass. <i>Pure and Applied Chemistry</i> , 2019, 91, 1757-1767.	1.9	4
23	Photoluminescence in pulsed-laser deposited GeGaSbS:Er films. <i>Optical Materials</i> , 2018, 85, 246-253.	3.6	1
24	Up-Conversion in Er ³⁺ -Doped Ge ₂₅ Ga ₅ Sb ₅ S ₆₅ Chalcogenide Glass for Enhancement of Silicon Solar Cell Efficiency. , 2012, , .		0